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(54) **SOLAR CELL AND METHOD FOR
MANUFACTURING THE SAME**

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See application file for complete search history.

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(56) **References Cited**

U.S. PATENT DOCUMENTS

4,219,830 A * 8/1980 Gibbons 136/255
6,313,397 B1 * 11/2001 Washio et al. 136/256
6,387,726 B1 5/2002 Verlinden et al.

(Continued)

FOREIGN PATENT DOCUMENTS

CN 1862840 A 11/2006
CN 101097969 A 1/2008

(Continued)

OTHER PUBLICATIONS

Lu et al., Rear surface passivation of interdigitated back contact
silicon heterojunction solar cell and 2D simulation study, 33rd IEEE
Photovoltaic Specialist Conference, May 11-16, 2008.

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(57) **ABSTRACT**

A solar cell and a method for manufacturing the same are
disclosed. The solar cell includes a substrate that contains first
impurities of a first conductive type and is formed of a crys-
talline semiconductor, a first field region that is positioned on
an incident surface of the substrate and contains second impu-
rities of a second conductive type, an emitter region that
contains third impurities of a third conductive type, is formed
of a non-crystalline semiconductor, and is positioned on a
non-incident surface of the substrate opposite the incident
surface of the substrate, a first electrode electrically con-
nected to the emitter region, and a second electrode electri-
cally connected to the substrate.

5 Claims, 8 Drawing Sheets

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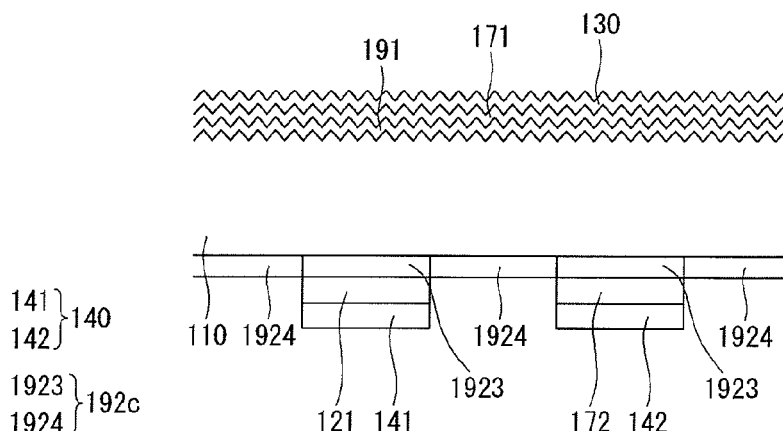
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Y02E 10/547 (2013.01)

(58) **Field of Classification Search**

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(56)

References Cited

U.S. PATENT DOCUMENTS

6,927,417	B2	8/2005	Nagashima et al.	
7,339,110	B1	3/2008	Mulligan et al.	
7,468,485	B1	12/2008	Swanson	
2004/0200520	A1 *	10/2004	Mulligan et al.	136/256
2004/0259335	A1 *	12/2004	Narayanan et al.	438/584
2006/0196535	A1	9/2006	Swanson et al.	
2006/0255340	A1	11/2006	Manivannan et al.	
2007/0169808	A1 *	7/2007	Kherani et al.	136/258
2008/0000522	A1	1/2008	Johnson et al.	
2008/0076203	A1 *	3/2008	Ribeyron et al.	438/72
2008/0156370	A1 *	7/2008	Abdallah et al.	136/258
2008/0173347	A1	7/2008	Korevaar et al.	
2008/0283490	A1	11/2008	Luan et al.	
2009/0014063	A1	1/2009	Stangl et al.	
2009/0151784	A1	6/2009	Luan et al.	
2009/0211623	A1 *	8/2009	Meier et al.	136/246
2009/0223562	A1 *	9/2009	Niira et al.	136/256
2009/0227061	A1 *	9/2009	Bateman et al.	438/57
2009/0227095	A1 *	9/2009	Bateman et al.	438/514
2009/0266401	A1 *	10/2009	Stangl et al.	136/244

2009/0308438	A1 *	12/2009	De Ceuster et al.	136/255
2010/0055822	A1 *	3/2010	Weidman et al.	438/57
2010/0193027	A1 *	8/2010	Ji et al.	136/256
2011/0000532	A1	1/2011	Niira et al.	
2011/0143480	A1 *	6/2011	Hilali et al.	438/58

FOREIGN PATENT DOCUMENTS

CN	101401215	A	4/2009	
EP	1 873 840	A1	1/2008	
JP	2003-152207	A	5/2003	
JP	2004-39751	A	2/2004	
JP	2009-524916	A	7/2009	
KR	10-2005-0039273	A	4/2005	
KR	2007-0079749	A	8/2007	
KR	100757797	B1	9/2007	
KR	10-2010-0068832	A	6/2010	
WO	WO 2007/140763	*	12/2007	H01L 31/068
WO	WO 2008/050889	*	5/2008	H01L 31/04
WO	WO 2009010585	A2 *	1/2009	H01L 31/0236
WO	WO 2009/096539	A1	8/2009	
WO	WO 2009/101107	A1	8/2009	

* cited by examiner

FIG. 1

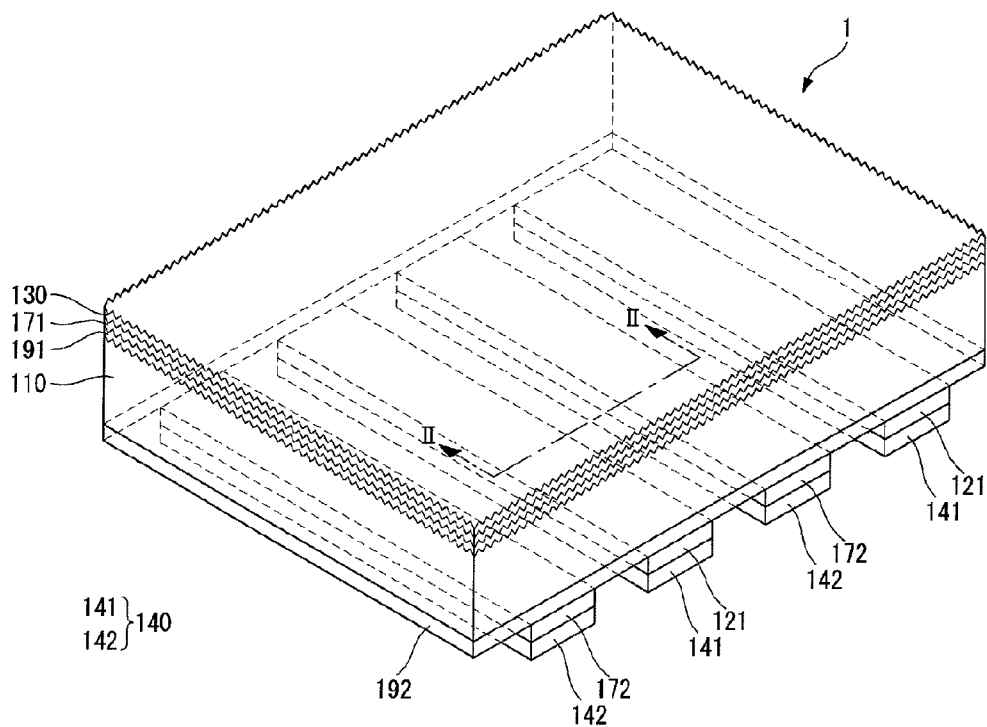


FIG. 2

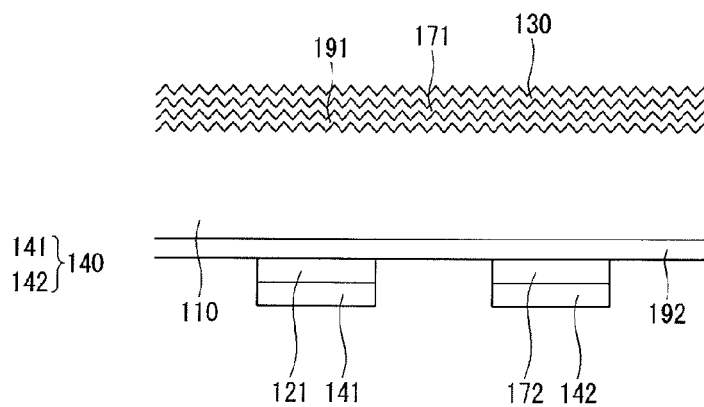


FIG. 3A

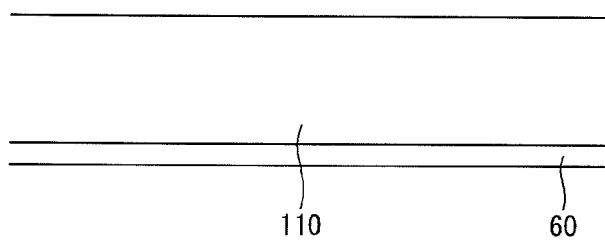


FIG. 3B

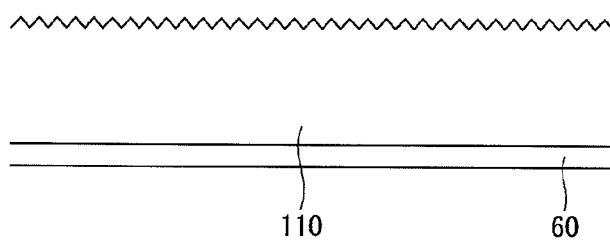


FIG. 3C

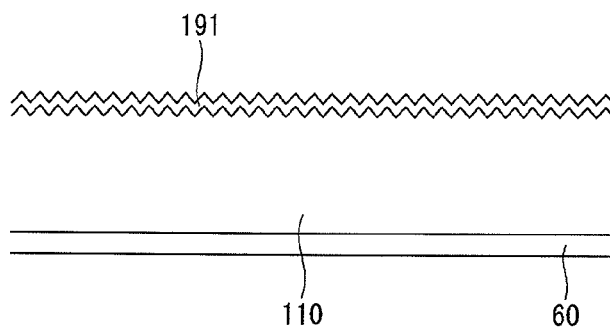


FIG. 3D

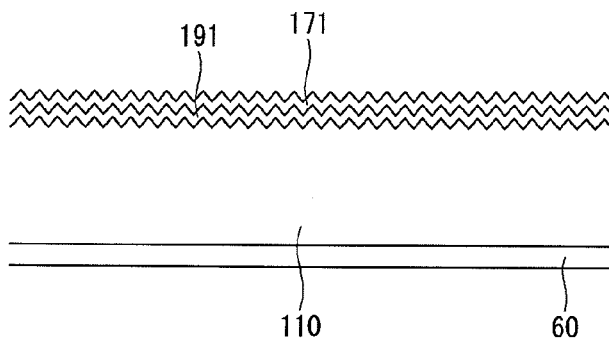


FIG. 3E

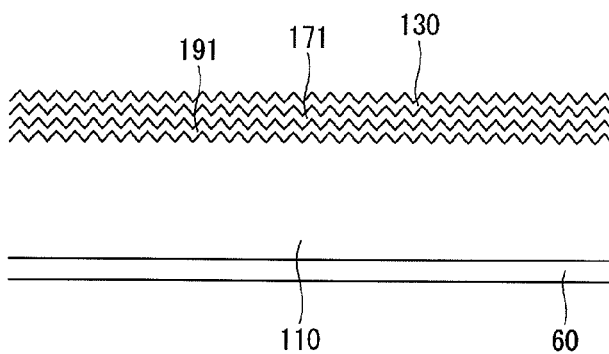


FIG. 3F

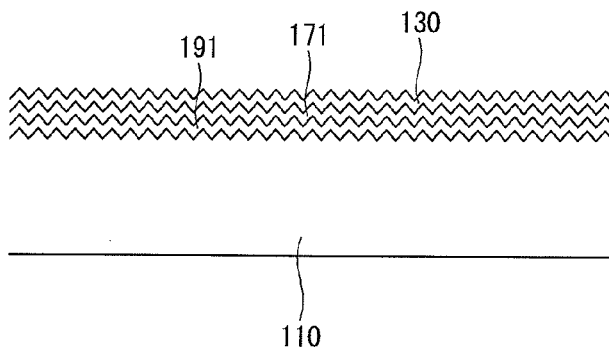


FIG. 3G

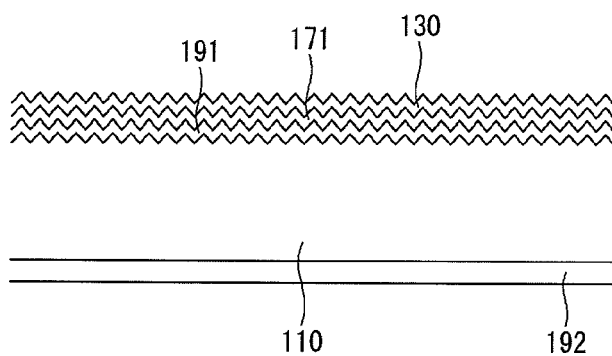


FIG. 3H

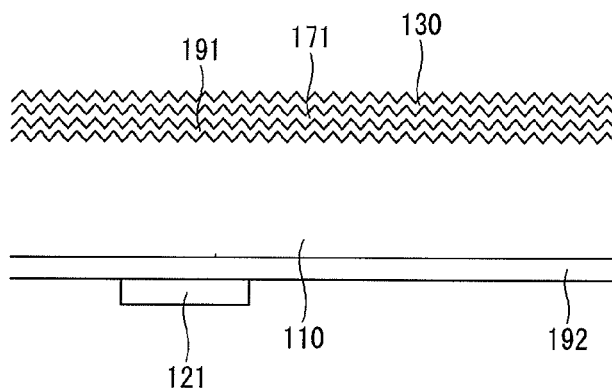


FIG. 3I

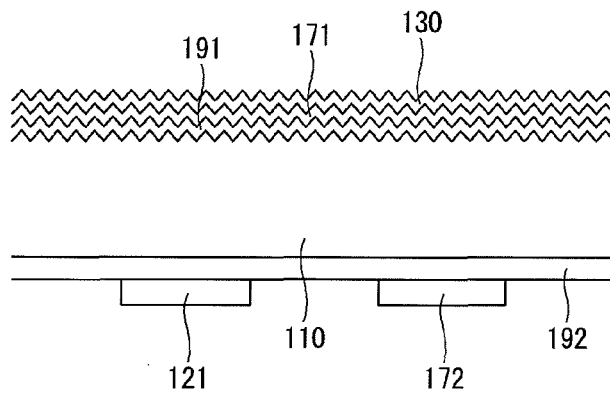


FIG. 3J

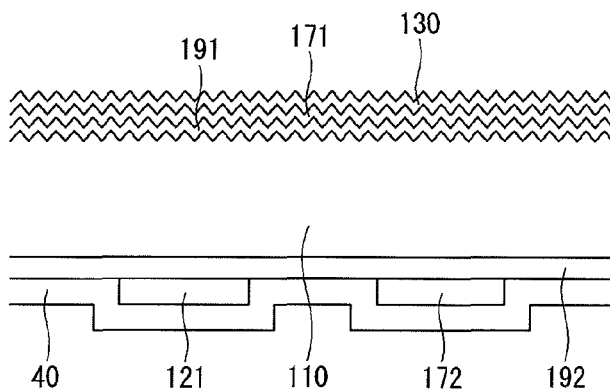


FIG. 4

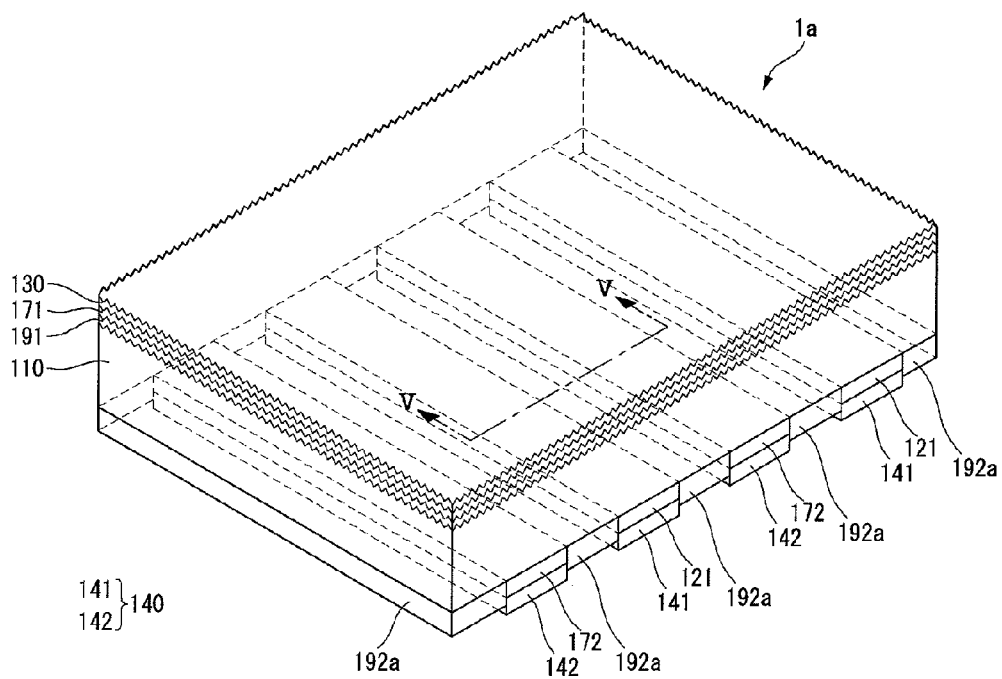


FIG. 5

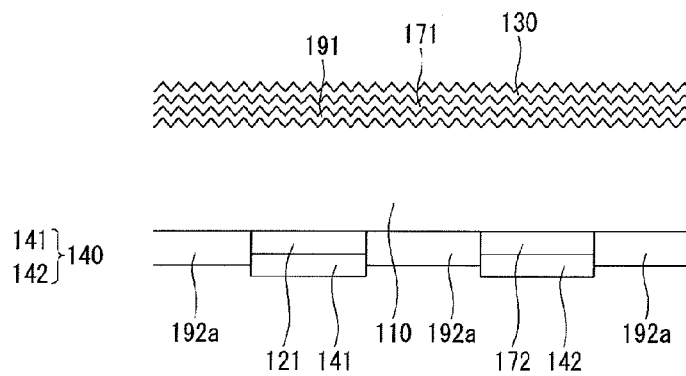


FIG. 6

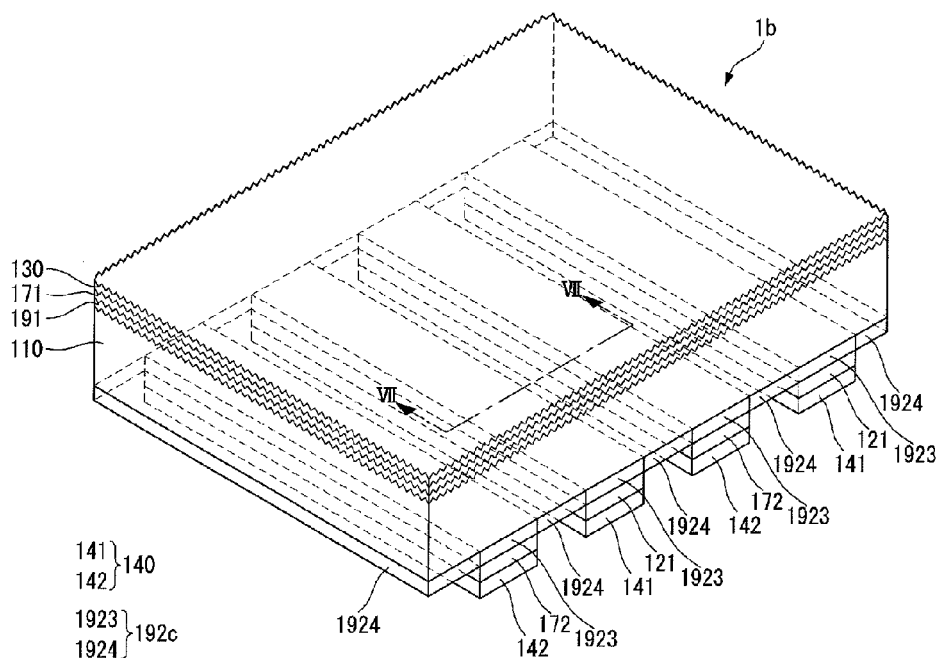


FIG. 7

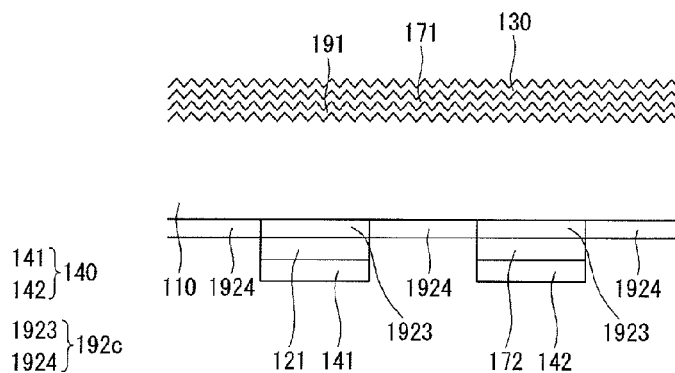
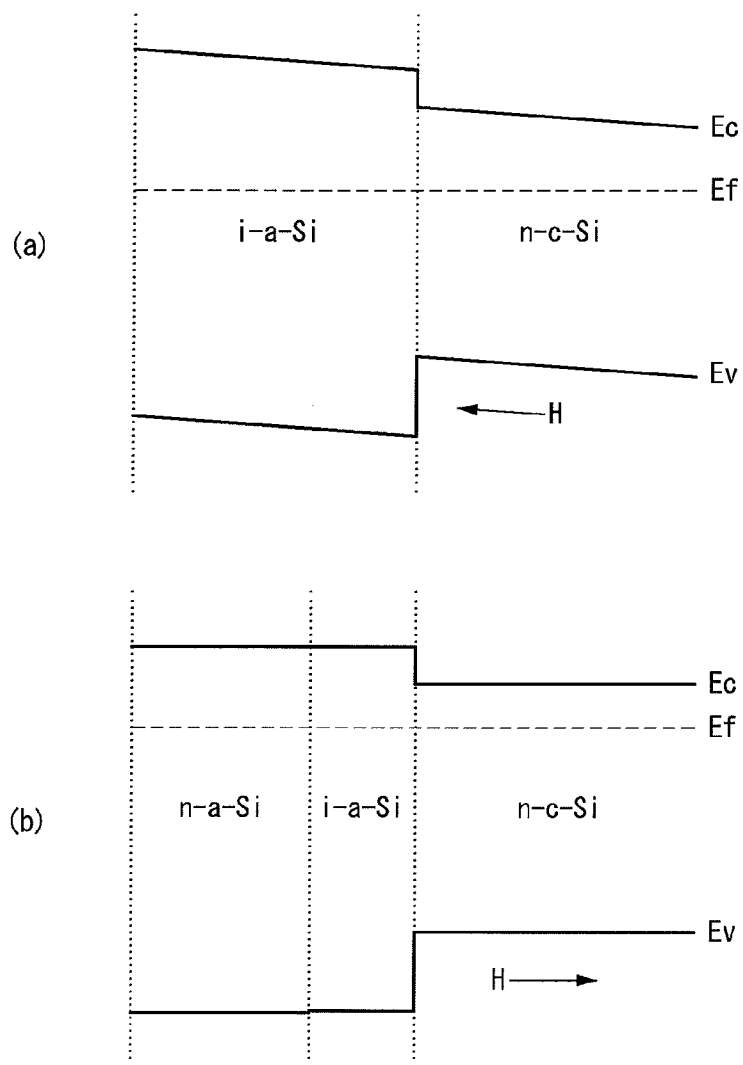


FIG. 8

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SOLAR CELL AND METHOD FOR MANUFACTURING THE SAME

This application claims priority to and the benefit of Korean Patent Application No. 10-2009-0084046, 10-2010-0043961 and 10-2010-0075028 filed in the Korean Intellectual Property Office on Sep. 7, 2009, May 11, 2010, and Aug. 3, 2010, respectively. The contents of which are incorporated herein by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

Embodiments of the invention relate to a solar cell and a method for manufacturing the same.

2. Description of the Related Art

Recently, as existing energy sources such as petroleum and coal are expected to be depleted, interests in alternative energy sources for replacing the existing energy sources are increasing. Among the alternative energy sources, solar cells for generating electric energy from solar energy have been particularly spotlighted.

A solar cell generally includes semiconductor parts that have different conductive types, such as a p-type and an n-type, and form a p-n junction, and electrodes respectively connected to the semiconductor parts of the different conductive types.

When light is incident on the solar cell, a plurality of electron-hole pairs are generated in the semiconductor parts. The electron-hole pairs are separated into electrons and holes by the photovoltaic effect. Thus, the separated electrons move to the n-type semiconductor and the separated holes move to the p-type semiconductor, and then the electrons and holes are collected by the electrodes electrically connected to the n-type semiconductor and the p-type semiconductor, respectively. The electrodes are connected to each other using electric wires to thereby obtain electric power.

SUMMARY OF THE INVENTION

In one aspect there is a solar cell including a substrate that contains first impurities of a first conductive type and is formed of a crystalline semiconductor, a first field region that is positioned on an incident surface of the substrate, and contains second impurities of a second conductive type, an emitter region that contains third impurities of a third conductive type, is formed of a non-crystalline semiconductor, and is positioned on a non-incident surface of the substrate opposite the incident surface of the substrate, a first electrode electrically connected to the emitter region, and a second electrode electrically connected to the substrate.

The solar cell may further include a first passivation layer positioned between the substrate and the first field region.

A concentration of the second impurities contained in the first field region may be higher than a concentration of the first impurities contained in the substrate. The concentration of the second impurities contained in the first field region may be approximately 1×10^{16} atoms/cm³ to 1×10^{21} atoms/cm³.

The first field region may have a thickness of 1 nm to 20 nm, and the first passivation layer may have a thickness of approximately 2 nm to 20 nm.

A concentration of the second impurities contained in the first field region may vary over a thickness of the first field region. The concentration of the second impurities contained in the first field region may increase from a contact surface between the first passivation layer and the first field region to an upper surface of the first field region. A minimum concen-

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tration of the second impurities of the first field region may be approximately 1×10^{10} atoms/cm³, and a maximum concentration of the second impurities of the first field region may be approximately 1×10^{21} atoms/cm³.

The first field region may have a thickness of 3 nm to 30 nm, and the first passivation layer may have a thickness of approximately 1 nm to 10 nm.

The first field region may be formed of amorphous silicon, amorphous silicon oxide, or amorphous silicon carbide.

The first passivation layer may be formed of intrinsic amorphous silicon.

The solar cell may further include a second field region that is positioned in the non-incident surface of the substrate to be separated from the emitter region. The second field region may have the same conductive type as the first field region.

The first conductive type may be the same as the second conductive type and may be opposite to the third conductive type.

The solar cell may further include a second passivation layer positioned on the non-incident surface of the substrate. The second passivation layer may be positioned on the substrate between the emitter region and the second field region. The second passivation layer may be positioned under the emitter region and under the second field region.

In another aspect, there is a solar cell including a substrate of a first conductive type, and is formed of a crystalline semiconductor, a field region of the first conductivity type and is positioned on an incident surface of the substrate, an anti-reflection layer directly positioned on the field region, an emitter region of a second conductive type different from the first conductive type, is formed of a non-crystalline semiconductor, and is positioned on a non-incident surface of the substrate opposite the incident surface of the substrate, a first electrode electrically connected to the emitter region, and a second electrode electrically connected to the substrate.

A concentration of impurities contained in the field region may be higher than a concentration of impurities contained in the substrate. The concentration of the impurities contained in the field region may be approximately 1×10^{16} atoms/cm³ to 1×10^{21} atoms/cm³.

The anti-reflection layer may be formed of at least one of silicon nitride, silicon oxide, and transparent metal oxide.

The solar cell may further include a passivation layer positioned between the substrate and the field region.

In another aspect, there is a method for manufacturing a solar cell including forming an emitter region containing first conductivity type impurities on a first surface of a substrate, forming a first field region containing second conductivity type impurities on the first surface of the substrate so that the first field region is separated from the emitter region, forming a passivation layer on a second surface, on which light is incident, opposite the first surface of the substrate, forming a second field region containing the second conductivity type impurities on the passivation layer, and forming a first electrode connected to the emitter region and a second electrode connected to the first field region.

A conductive type of the first conductivity type impurities may be opposite to a conductive type of the second conductivity type impurities.

The forming of the second field region may include keeping an injection rate of the second conductivity type impurities injected into a process chamber constant or varying the injection rate of the second conductivity type impurities injected into the process chamber as time has passed.

The substrate may be formed of a crystalline semiconductor, and the emitter region may be formed of a non-crystalline semiconductor.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this specification, illustrate embodiments of the invention and together with the description serve to explain the principles of the invention. In the drawings:

FIG. 1 is a partial perspective view of a solar cell according to an example embodiment of the invention;

FIG. 2 is a cross-sectional view taken along line II-II of FIG. 1;

FIGS. 3A to 3J sequentially illustrate each of stages in a method for manufacturing the solar cell shown in FIG. 1;

FIG. 4 is a partial perspective view of a solar cell according to another example embodiment of the invention;

FIG. 5 is a cross-sectional view taken along line V-V of FIG. 4;

FIG. 6 is a partial perspective view of a solar cell according to another example embodiment of the invention;

FIG. 7 is a cross-sectional view taken along line VII-VII of FIG. 6; and

FIG. 8 schematically illustrates an energy band gap state of a substrate when a front surface field region is not positioned on the substrate and an energy band gap state of the substrate when the front surface field region is positioned on the substrate.

DETAILED DESCRIPTION OF THE EMBODIMENTS

The invention will be described more fully hereinafter with reference to the accompanying drawings, in which example embodiments of the inventions are shown. This invention may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein.

In the drawings, the thickness of layers, films, panels, regions, etc., are exaggerated for clarity. Like reference numerals designate like elements throughout the specification. It will be understood that when an element such as a layer, film, region, or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present. In contrast, when an element is referred to as being "directly on" another element, there are no intervening elements present. Further, it will be understood that when an element such as a layer, film, region, or substrate is referred to as being "entirely" on another element, it may be on the entire surface of the other element and may not be on a portion of an edge of the other element.

Reference will now be made in detail to embodiments of the invention, examples of which are illustrated in the accompanying drawings.

A solar cell according to an example embodiment of the invention is described in detail with reference to FIGS. 1 and 2.

FIG. 1 is a partial perspective view of a solar cell according to an example embodiment of the invention. FIG. 2 is a cross-sectional view taken along line II-II of FIG. 1.

As shown in FIGS. 1 and 2, a solar cell 1 according to an example embodiment of the invention includes a substrate 110, a front passivation layer 191 positioned on an incident surface (hereinafter, referred to as "a front surface") of the substrate 110 on which light is incident, a front surface field (FSF) region 171 positioned on the front passivation layer 191, an anti-reflection layer 130 positioned on the FSF region

171, a back passivation layer 192 positioned on a surface (hereinafter, referred to as "a back surface") of the substrate 110, on which the light is not incident, opposite the front surface of the substrate 110, a plurality of emitter regions 121 positioned on the back passivation layer 192, a plurality of back surface field (BSF) regions 172 that are positioned on the back passivation layer 192 to be separated from the plurality of emitter regions 121, and an electrode part 140 including a plurality of first electrodes 141 respectively positioned on the plurality of emitter regions 121 and a plurality of second electrodes 142 respectively positioned on the plurality of BSF regions 172.

The substrate 110 is a semiconductor substrate formed of first conductive type silicon, for example, n-type silicon, though not required. Silicon used in the substrate 110 may be crystalline silicon such as single crystal silicon and polycrystalline silicon. When the substrate 110 is of an n-type, the substrate 110 is doped with impurities of a group V element such as phosphor (P), arsenic (As), and antimony (Sb). Alternatively, the substrate 110 may be of a p-type, and/or be formed of another semiconductor materials other than silicon. When the substrate 110 is of the p-type, the substrate 110 is doped with impurities of a group III element such as boron (B), gallium (Ga), and indium (In).

The front surface of the substrate 110 may be textured to form a textured surface corresponding to an uneven surface or having uneven characteristics. For convenience, FIG. 1 shows that only an edge portion of the substrate 110 has the textured surface and only edge portions of the front passivation layer 191, the FSF region 171, and the anti-reflection layer 130 on the front surface of the substrate 110 have the textured surface. However, the entire front surface of the substrate 110 has really the textured surface, and thus the front passivation layer 191, the FSF region 171, and the anti-reflection layer 130 on the front surface of the substrate 110 have the textured surface.

The back surface as well as the front surface of the substrate 110 may have a textured surface. In this instance, all of the back passivation layer 192, the plurality of emitter regions 121, the plurality of BSF regions 172, and the electrode part 140 positioned on the back surface of the substrate 110 may have an uneven surface.

The front passivation layer 191 on the front surface of the substrate 110 is formed of intrinsic amorphous silicon (a-Si). The front passivation layer 191 performs a passivation operation that converts a defect, for example, dangling bonds existing on the surface of the substrate 110 and around the surface of the substrate 110 into stable bonds to thereby prevent or reduce a recombination and/or a disappearance of carriers moving to the front surface of the substrate 110 resulting from the defect. Hence, the front passivation layer 191 reduces a loss amount of carriers caused to disappear by the defect on or around the surface of the substrate 110.

In general, the defect mostly exists on or around the surface of the substrate 110. Thus, in the embodiment of the invention, because the front passivation layer 191 directly contacts the surface of the substrate 110, a passivation effect is further improved. Hence, a loss amount of carriers is further reduced.

In the embodiment of the invention, the front passivation layer 191 may have a thickness of approximately 1 nm to 20 nm. When the thickness of the front passivation layer 191 is equal to or greater than approximately 1 nm, the passivation operation may be well performed because the front passivation layer 191 is uniformly applied to the front surface of the substrate 110. When the thickness of the front passivation layer 191 is equal to or less than approximately 20 nm, an

amount of light absorbed in the front passivation layer 191 is reduced. Hence, an amount of light incident in the substrate 110 may increase.

The FSF region 171 on the front passivation layer 191 is an impurity region that is more heavily doped with impurities of the same conductive type (for example, the n-type) as the substrate 110 than the substrate 110. In the embodiment of the invention, an impurity concentration of the FSF region 171 may be at least approximately 1×10^{10} atoms/cm³ and may be at most approximately 1×10^{21} atoms/cm³. The FSF region 171 may be formed of amorphous silicon, amorphous silicon oxide (a-SiOx), or amorphous silicon carbide (a-SiC).

The movement of carriers (for example, holes) to the front surface of the substrate 110 is prevented or reduced by a potential barrier resulting from a difference between impurity concentrations of the substrate 110 and the FSF region 171. Thus, a front surface field effect is obtained by returning the carriers moving to the front surface of the substrate 110 to the back surface of the substrate 110 by the potential barrier. Hence, an output amount of carriers output to an external device increases, and a recombination and/or a disappearance of carriers at the front surface of the substrate 110 are prevented or reduced.

In general, energy band gaps of amorphous silicon oxide (a-SiOx) and amorphous silicon carbide (a-SiC) are approximately 2.1 eV and 2.8 eV, respectively. The energy band gaps are wide than amorphous silicon having an energy band gap of approximately 1.7 eV to eV 1.9. Thus, when the FSF region 171 is formed of amorphous silicon oxide (a-SiOx) or amorphous silicon carbide (a-SiC), a waveform region of light absorbed in the FSF region 171 decreases. Hence, an amount of light absorbed in the FSF region 171 decreases, and an amount of light incident on the substrate 110 further increases.

In the present embodiment, the impurity concentration of the FSF region 171 continuously or discontinuously changes in the range of approximately 1×10^{10} atoms/cm³ to 1×10^{21} atoms/cm³ along (or in) a thickness direction, or is substantially uniform in the range of approximately 1×10^{16} atoms/cm³ to 1×10^{21} atoms/cm³ along (or in) the thickness direction.

When the impurity concentration of the FSF region 171 changes in the range of approximately 1×10^{10} atoms/cm³ to 1×10^{21} atoms/cm³ along the thickness direction, a portion of the FSF region 171 performs the passivation operation in the same manner as the front passivation layer 191. In this instance, the impurity concentration of the FSF region 171 changes from an impurity concentration at a portion of the FSF region 171 adjoining the front passivation layer 191 to an impurity concentration at a portion of the FSF region 171 adjoining the anti-reflection layer 130.

For example, in the FSF region 171 that is closer to the front passivation layer 191, the impurity concentration of the FSF region 171 decreases. On the contrary, in the FSF region 171 that is closer to the anti-reflection layer 130, the impurity concentration of the FSF region 171 increases. A portion of the FSF region 171 positioned at a shortest distance between the portion of the FSF region 171 adjoining the front passivation layer 191 and the surface of the substrate 110, has a minimum impurity concentration. A portion of the FSF region 171 positioned at a shortest distance between the portion of the FSF region 171 adjoining the anti-reflection layer 130 and the surface of the substrate 110, has a maximum impurity concentration. In this instance, the two shortest distances are measured from the same portion or position of the substrate 110.

Accordingly, the minimum impurity concentration is approximately 1×10^{10} atoms/cm³, and the maximum impurity concentration is approximately 1×10^{21} atoms/cm³ in the FSF region 171.

In this instance, because the FSF region 171 performs the passivation operation as well as a front surface field operation, a thickness of the FSF region 171 has to be greater than a thickness of the FSF region when the FSF region performs only the front surface field operation. Further, a thickness of the front passivation layer 191 may slightly decrease. In this instance, the front passivation layer 191 may have a thickness of approximately 1 nm to 10 nm, and the FSF region 171 may have a thickness of approximately 3 nm to 30 nm.

When the thickness of the front passivation layer 191 is equal to or greater than approximately 1 nm, the passivation efficiency may further increase because the front passivation layer 191 is uniformly applied to the front surface of the substrate 110. When the thickness of the front passivation layer 191 is equal to or less than approximately 10 nm, an amount of light incident on the substrate 110 may further increase because the front passivation layer 191 performs the passivation operation without the absorption of light in the front passivation layer 191.

When the thickness of the FSF region 171 is equal to or greater than approximately 3 nm, the FSF region 171 may generate a field strength capable of stably performing the front surface field operation even if a portion of the FSF region 171 perform the passivation operation. Further, the FSF region 171 may form an electric field with a normal size irrespective of the presence of the front passivation layer 191, that is positioned between the substrate 110 and the FSF region 171 and which adversely affects a field strength reacting on (or applied to) the substrate 110, thereby stably performing the front surface field operation. When the thickness of the FSF region 171 is equal to or less than approximately 30 nm, an amount of light incident on the substrate 110 may further increase because the FSF region 171 performs the front surface field operation without the absorption of light in the FSF region 171.

Alternatively, when the FSF region 171 has substantially the uniform impurity concentration, the impurity concentration of the FSF region 171 may be substantially uniform irrespective of changes in the thickness of the FSF region 171. In this instance, because the FSF region 171 mainly performs the front surface field operation for the front surface field effect as compared with the passivation operation thereof, the FSF region 171 has to have the impurity concentration capable of smoothly performing the front surface field operation using the difference between the impurity concentrations of the substrate 110 and the FSF region 171.

Accordingly, when the FSF region 171 mainly performs the front surface field operation, the impurity concentration of the FSF region 171 has to be one that is higher than the impurity concentration of the FSF region 171 when the portion of the FSF region 171 performs the passivation operation. Further, the impurity concentration of the FSF region 171 may be higher than the impurity concentration of the substrate 110. In the present embodiment, the FSF region 171 has substantially the uniform impurity concentration belonging to the range of approximately 1×10^{16} atoms/cm³ to 1×10^{21} atoms/cm³.

When the FSF region 171 mainly performs the front surface field operation as compared with the passivation operation, the thickness of the front passivation layer 191 underlying the FSF region 171 may slightly increase for sake of the stable passivation operation, and the thickness of the FSF region 171 may slightly decrease because the FSF region 171

mainly performs the front surface field operation. Hence, the thickness of the front passivation layer **191** may be approximately 2 nm to 20 nm, and the thickness of the FSF region **171** may be approximately 1 nm to 20 nm.

When the thickness of the front passivation layer **191** is equal to or greater than approximately 2 nm, the defect existing on or around the surface of the substrate **110** may be completely removed by use of only the front passivation layer **191**. Hence, the front passivation layer **191** may excellently perform the passivation operation. When the thickness of the front passivation layer **191** is equal to or less than approximately 20 nm, an amount of light incident on the substrate **110** may further increase because the front passivation layer **191** performs the passivation operation without the absorption of light in the front passivation layer **191**.

When the thickness of the FSF region **171** is equal to or greater than approximately 1 nm, the FSF region **171** may form an electric field with the normal size irrespective of the presence of the front passivation layer **191**, that is positioned between the substrate **110** and the FSF region **171**, and which adversely affects the electric field strength reacting on or applied to the substrate **110**, thereby stably performing the front surface field operation. When the thickness of the FSF region **171** is equal to or less than approximately 20 nm, an amount of light incident on the substrate **110** may further increase because the FSF region **171** performs the front surface field operation without the absorption of light in the FSF region **171**.

The anti-reflection layer **130** on the FSF region **171** reduces a reflectance of light incident on the solar cell **1** and increases selectivity of a predetermined wavelength band, thereby increasing the efficiency of the solar cell **1**.

The anti-reflection layer **130** may be formed of silicon oxide (SiOx) and/or silicon nitride (SiNx).

Further, the anti-reflection layer **130** may be formed using transparent metal oxide formed of at least one selected from the group consisting of indium tin oxide (ITO), tin (Sn)-based oxide (for example, SnO₂), zinc (Zn)-based oxide (for example, ZnO, ZnO:Al, ZnO:B, and AZO), and a combination thereof. A transparency and insulating characteristic of the transparent metal oxide vary depending on oxygen (O₂) content. Namely, as the O₂ content increases, a transparency of the transparent metal oxide increases and a transmittance of light increases. Further, when the O₂ content exceeds a predetermined content, the transparent metal oxide represents non-conductive characteristics because resistivity of the transparent metal oxide increases to an infinite value. Hence, the transparent metal oxide changes to an insulating material. Accordingly, the transparent metal oxide according to the embodiment of the invention is a transparent conductive oxide (TCO) or a transparent insulating oxide (TIO) depending on the O₂ content.

The transparency of the transparent metal oxide is greater than transparencies of silicon oxide (SiOx) and silicon nitride (SiNx). Thus, when the anti-reflection layer **130** is formed of the transparent metal oxide, an amount of light incident inside the substrate **110** further increases. Hence, the efficiency of the solar cell **1** is further improved.

In the present embodiment, the anti-reflection layer **130** has a single-layered structure, but may have a multi-layered structure such as a double-layered structure in other embodiments. The anti-reflection layer **130** may be omitted, if desired.

The back passivation layer **192** directly positioned on the back surface of the substrate **110** performs the passivation operation in the same manner as the front passivation layer

191, thereby preventing or reducing a recombination and/or a disappearance of carriers moving to the back surface of the substrate **110**.

The back passivation layer **192** may be formed of amorphous silicon in the same manner as the front passivation layer **191**.

The back passivation layer **192** has a thickness to the extent that carriers moving to the back surface of the substrate **110** can pass through the back passivation layer **192** and can move to the BSF regions **172** and the emitter regions **121**. In the present embodiment, the thickness of the back passivation layer **192** may be approximately 1 nm to 10 nm.

When the thickness of the back passivation layer **192** is equal to or greater than approximately 1 nm, the passivation effect may be further obtained or may be greater because the back passivation layer **192** is uniformly applied to the back surface of the substrate **110**. When the thickness of the back passivation layer **192** is equal to or less than approximately 10 nm, an amount of light passing through the substrate **110** absorbed in the back passivation layer **192** is reduced. Hence, an amount of light again incident inside the substrate **110** may further increase.

Each of the plurality of BSF regions **172** is an impurity region that is more heavily doped with impurities of the same conductive type as the substrate **110** than the substrate **110**. For example, each BSF region **172** may be an n⁺-type region.

The plurality of BSF regions **172** extend parallel to one another on the back passivation layer **192** in a fixed direction to be separated from one another. In the present embodiment, the BSF regions **172** are formed of a non-crystalline semiconductor such as amorphous silicon.

The BSF regions **172** prevent or reduce the movement of holes to the BSF regions **172** used as a moving path of electrons by a potential barrier resulting from a difference between impurity concentrations of the substrate **110** and the BSF regions **172** in the same manner as the FSF region **171**. Further, the BSF regions **172** facilitate the movement of carriers (for example, electrons) to the BSF regions **172**. Thus, the BSF regions **172** reduce a loss amount of carriers by a recombination and/or a disappearance of electrons and holes in or around the BSF regions **172** or in the electrode part **140** and accelerate the movement of electrons to the BSF regions **172**, thereby increasing an amount of electrons moving to the BSF regions **172**.

Each BSF region **172** may have a thickness of approximately 10 nm to 25 nm. When the thickness of the BSF region **172** is equal to or greater than approximately 10 nm, the BSF region **172** may form a potential barrier sufficient to prevent or reduce the movement of holes to the BSF region **172** to thereby further reduce a loss amount of carriers. When the thickness of the BSF region **172** is equal to or less than approximately 25 nm, the BSF region **172** further reduces an amount of light absorbed in the BSF region **172** to thereby further increase an amount of light again incident inside the substrate **110**.

The plurality of emitter regions **121** are positioned on the back surface of the substrate **110** to be separated from the BSF regions **172** and extend parallel to the BSF regions **172**.

As shown in FIGS. 1 and 2, the plurality of emitter regions **121** and the plurality of BSF regions **172** are alternately positioned on the back surface of the substrate **110**.

Each emitter region **121** is of a second conductive type (for example, a p-type) opposite a conductive type of the substrate **110**. Each emitter region **121** is formed of a semiconductor, for example, amorphous silicon different from the substrate **110**. Thus, the plurality of emitter regions **121** and the substrate **110** form a heterojunction as well as a p-n junction.

A plurality of electron-hole pairs produced by light incident on the substrate **110** are separated into electrons and holes by a built-in potential difference resulting from the p-n junction between the substrate **110** and the emitter regions **121**. Then, the separated electrons move to the n-type semiconductor, and the separated holes move to the p-type semiconductor. Thus, when the substrate **110** is of the n-type and the emitter regions **121** are of the p-type, the separated holes pass through the back passivation layer **192** and move to the emitter regions **121** and the separated electrons pass through the back passivation layer **192** and move to the BSF regions **172** having the impurity concentration higher than the substrate **110**.

Because the substrate **110** and each emitter region **121** form the p-n junction, the emitter region **121** may be of the n-type when the substrate **110** is of the p-type unlike the embodiment described above. In this instance, the separated electrons pass through the back passivation layer **192** and move to the emitter regions **121**, and the separated holes pass through the back passivation layer **192** and move to the BSF regions **172**.

When the plurality of emitter regions **121** are of the p-type, the emitter regions **121** may be doped with impurities of a group III element. On the contrary, when the emitter regions **121** are of the n-type, the emitter regions **121** may be doped with impurities of a group V element.

The plurality of emitter regions **121** may perform the passivation operation along with the back passivation layer **192**. In this instance, an amount of carriers caused to disappear at the back surface of the substrate **110** by the defect is reduced, and thus the efficiency of the solar cell **1** is improved.

Each emitter region **121** may have a thickness of 5 nm to 15 nm. When the thickness of the emitter region **121** is equal to or greater than approximately 5 nm, the emitter region **121** may form a good p-n junction. When the thickness of the emitter region **121** is equal to or less than approximately 15 nm, an amount of light absorbed in the emitter region **121** is further reduced. Hence, an amount of light again incident inside the substrate **110** may further increase.

In the present embodiment, a crystallization phenomenon obtained when the emitter regions **121** and the BSF regions **172** are positioned on the back passivation layer **192** is reduced further than a crystallization phenomenon obtained when the emitter regions **121** and the BSF regions **172** are positioned directly on the substrate **110** formed of a crystalline semiconductor material, because the back passivation layer **192** is formed of intrinsic amorphous silicon (a-Si) in which there is no impurities or scarcely any impurities. Hence, characteristics of the emitter regions **121** and the BSF regions **172** positioned on an amorphous silicon layer (i.e., the back passivation layer **192**) are improved.

The plurality of first electrodes **141** on the plurality of emitter regions **121** long extend along the emitter regions **121** and are electrically and physically connected to the emitter regions **121**. Each first electrode **141** collects carriers (for example, holes) moving to the corresponding emitter region **121**.

The plurality of second electrodes **142** on the plurality of BSF regions **172** long extend along the BSF regions **172** and are electrically and physically connected to the BSF regions **172**. Each second electrode **142** collects carriers (for example, electrons) moving to the corresponding BSF region **172**.

In FIGS. **1** and **2**, the first and second electrodes **141** and **142** have the same plane shape or sheet shape as the emitter regions **121** and the BSF regions **172** underlying the first and second electrodes **141** and **142**. However, they may have

different plane shapes. As a contact area between the emitter regions **121** and the BSF regions **172** and the respective first and second electrodes **141** and **142** increases, a contact resistance therebetween decreases. Hence, the carrier transfer efficiency of the first and second electrodes **141** and **142** increases.

The plurality of first and second electrodes **141** and **142** may be formed of at least one conductive material selected from the group consisting of nickel (Ni), copper (Cu), silver (Ag), aluminum (Al), tin (Sn), zinc (Zn), indium (In), titanium (Ti), gold (Au), and a combination thereof. Other conductive materials may be used. As described above, because the plurality of first and second electrodes **141** and **142** are formed of the metal material, the plurality of first and second electrodes **141** and **142** reflect light passing through the substrate **110** onto the substrate **110**.

The solar cell **1** having the above-described structure is a solar cell in which the plurality of first and second electrodes **141** and **142** are positioned on the back surface of the substrate **110**, on which light is not incident, and the substrate **110** and the plurality of emitter regions **121** are formed of different kinds of semiconductors. An operation of the solar cell **1** is described below.

When light is irradiated onto the solar cell **1**, sequentially passes through the anti-reflection layer **130**, the FSF region **171**, and the front passivation layer **191**, and is incident on the substrate **110**, a plurality of electron-hole pairs are generated in the substrate **110** by light energy based on the incident light. In this instance, because the front surface of the substrate **110** is the textured surface, a reflectance of light at the front surface of the substrate **110** is reduced. Further, because both a light incident operation and a light reflection operation are performed on the textured surface of the substrate **110**, a light absorption increases and the efficiency of the solar cell **1** is improved. In addition, because a reflection loss of the light incident on the substrate **110** is reduced by the anti-reflection layer **130**, an amount of light incident on the substrate **110** further increases.

The electron-hole pairs are separated into electrons and holes by the p-n junction of the substrate **110** and the emitter regions **121**, and the separated holes move to the p-type emitter regions **121** and the separated electrons move to the n-type BSF regions **172**. The holes moving to the p-type emitter regions **121** are collected by the first electrodes **141**, and the electrons moving to the n-type BSF regions **172** are collected by the second electrodes **142**. When the first electrodes **141** and the second electrodes **142** are connected to each other using electric wires, current flows therein to thereby enable use of the current for electric power.

Further, because the passivation layers **192** and **191** are positioned on the front surface as well as the back surface of the substrate **110**, a loss amount of carriers caused to disappear by the defect on and around the front and back surfaces of the substrate **110** is reduced. Hence, the efficiency of the solar cell **1** is improved. In this instance, because the front passivation layer **191** as well as the back passivation layer **192** make direct contact with the surface of the substrate **110** in which the defect is frequently generated, the passivation effect is further improved.

Further, a loss amount of carriers is further reduced because of the FSF region **171** and the BSF region **172** respectively positioned on the front and back surfaces of the substrate **110**, and thus the efficiency of the solar cell **1** is further improved.

Next, an energy band gap when the front passivation layer and the FSF region are formed on the front surface of the solar cell and an energy band gap when only the front passivation

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layer is formed on the front surface of the solar cell are described with reference to FIG. 8.

(a) of FIG. 8 illustrates an energy band gap between the substrate and the front passivation layer when only the front passivation layer without the FSF region is directly positioned on the substrate. (b) of FIG. 8 illustrates an energy band gap between the substrate and the front passivation layer and the FSF region when the front passivation layer and the FSF region are sequentially positioned on the substrate.

For a solar cell for measuring the energy band gap shown in FIG. 8, the front passivation layer is formed of intrinsic amorphous silicon (i-a-Si) having a thickness of approximately 20 nm, the FSF region is formed of n-type amorphous silicon (n-a-Si) having a thickness of approximately 10 nm and an impurity concentration of approximately 1×10^{20} atoms/cm³, and the substrate is formed of n-type polycrystalline silicon (n-c-Si).

As shown in (a) of FIG. 8, when the FSF region is not present, an energy band gap of the substrate (n-c-Si) was inclined. Therefore, holes H having the energy band gap characteristic moving from a low energy level to a high energy level mainly moved to the front passivation layer (i-a-Si), i.e., the front surface of the substrate (n-c-Si), and a loss of holes H occurred between the substrate (n-c-Si) and the front passivation layer (i-a-Si).

However, as shown in (b) of FIG. 8, when the FSF region (n-a-Si) existed, an energy band gap of the substrate (n-c-Si) was almost held in a parallel state because of an electric field formed by the FSF region (n-a-Si). Therefore, a directional behavior of holes H to move to the front surface of the substrate (n-c-Si) is not present. Hence, a loss of holes H generated between the substrate (n-c-Si) and the front passivation layer (i-a-Si) was greatly reduced.

When the FSF region is not present at the front surface of the substrate, a short-circuit current of the solar cell was approximately 28.47 mA/cm². When the FSF region is present at the front surface of the substrate, a short-circuit current of the solar cell was approximately 35.05 mA/cm². Namely, the short-circuit current of the solar cell increased by approximately 30%. The solar cells illustrated in (a) and (b) of FIG. 8 were manufactured under the same conditions, except the absence or presence of the FSF region. As above, a loss amount of carriers at the back surface of the substrate is greatly reduced by the operation of the FSF region, and thus the short-circuit current of the solar cell increases.

A method for manufacturing the solar cell 1 according to the embodiment of the invention is described below with reference to FIGS. 3A to 3J.

FIGS. 3A to 3J sequentially illustrate each of stages in a method for manufacturing the solar cell shown in FIG. 1.

As shown in FIG. 3A, an etch stop layer 60 formed of silicon oxide (SiO_x), etc. is formed on the surface of the substrate 110 formed of n-type single crystal silicon or n-type polycrystalline silicon, for example.

Next, as shown in FIG. 3B, the surface (for example, the incident surface) of the substrate 110, on which the etch stop layer 60 is not formed is etched, while another surface is protected using the etch stop layer 60 as a mask, to form a textured surface having a plurality of uneven portions on the front surface (for example, the incident surface) of the substrate 110. When the substrate 110 is formed of single crystal silicon, the front surface of the substrate 110 may be textured using a basic solution such as KOH, NaOH, and tetramethylammonium hydroxide (TMAH). On the other hand, when the substrate 110 is formed of polycrystalline silicon, the front surface of the substrate 110 may be textured using an acid solution such as HF and HNO₃.

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If both the front surface and the back surface of the substrate 110 is to have the textured surface, the front surface and back surface of the substrate 110 may be exposed to an etchant or an etching gas without forming the etch stop layer 60 to form the textured surface on the front surface and the back surface of the substrate 110.

Next, as shown in FIG. 3C, the front passivation layer 191 formed of amorphous silicon is formed on the front surface (i.e., the textured surface) of the substrate 110 using a layer forming method such as a plasma enhanced chemical vapor deposition (PECVD) method.

Next, as shown in FIG. 3D, the FSF region 171 formed of amorphous silicon is formed on the front passivation layer 191 using the PECVD method, etc. In this instance, because the FSF region 171 has the same conductive type as the substrate 110, an impurity doping material (for example, POCl₃ or H₃PO₄) containing impurities of a group V element such as phosphor (P) is injected into a process chamber. Hence, the FSF region 171, that has the same conductive type as the substrate 110 and has an impurity concentration higher than the substrate 110, is formed.

The FSF region 171 thus formed may have the uniform impurity concentration irrespective of its thickness. In this instance, the impurity concentration of the FSF region 171 is approximately 1×10^{16} atoms/cm³ to 1×10^{21} atoms/cm³. An injection rate of the impurity doping material injected into the process chamber for forming the FSF region 171 is substantially uniform.

However, alternatively, the impurity concentration of the FSF region 171 thus formed may change continuously or discontinuously over the thickness of the FSF region 171. In this instance, the impurity concentration of the FSF region 171 changes in the range of approximately 1×10^{10} atoms/cm³ to 1×10^{21} atoms/cm³ over its thickness. With greater thickness of the FSF region 171, there is an increase of the impurity concentration of the FSF region 171. An injection rate of the impurity doping material injected into the process chamber for forming the FSF region 171 increases with time.

Next, as shown in FIG. 3E, the anti-reflection layer 130 formed of silicon oxide (SiO_x) and/or silicon nitride (SiN_x) is formed on the FSF region 171 using the PECVD method, etc.

Next, as shown in FIG. 3F, the etch stop layer 60 formed on the back surface of the substrate 110 is removed.

Next, as shown in FIG. 3G, the back passivation layer 192 is formed on the back surface of the substrate 110 using the PECVD method, etc. The back passivation layer 192 is formed of amorphous silicon, etc.

Next, as shown in FIG. 3H, after a mask having a plurality of openings is positioned on the back passivation layer 192, amorphous silicon is deposited using the PECVD method, etc., to form the plurality of emitter regions 121. When the plurality of emitter regions 121 are formed, an impurity doping material (for example, B₂H₆) containing impurities of a group III element such as boron (B) is injected into a process chamber. Therefore, the emitter regions 121 contain impurities of a conductivity type opposite the conductivity type of the substrate 110. Hence, the p-n junction between the substrate 110 and the plurality of emitter regions 121 is formed. Further, because the substrate 110 and the emitter regions 121 are formed of different semiconductor materials, the substrate 110 and the emitter regions 121 form the heterojunction.

Positions of the plurality of openings correspond to portions of the back passivation layer 192 on which the plurality of emitter regions 121 are formed, and thus the plurality of openings expose the portions of the back passivation layer 192 on which the plurality of emitter regions 121 are formed.

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Next, as shown in FIG. 3I, after a mask having a plurality of openings is positioned on the back passivation layer 192, amorphous silicon is deposited using the PECVD method, etc., to form the plurality of BSF regions 172. Because the plurality of BSF regions 172 are formed by injecting an impurity doping material containing impurities of a group V element such as phosphor (P) into the process chamber, the plurality of BSF regions 172 become impurity regions having an impurity concentration higher than the substrate 110.

In this instance, positions of the plurality of openings correspond to portions of the back passivation layer 192 on which the plurality of BSF regions 172 are formed, and thus the plurality of openings expose the portions of the back passivation layer 192 on which the plurality BSF regions 172 are formed.

The formation order of the emitter regions 121 and the BSF regions 172 may vary. The emitter regions 121 and the BSF regions 172 may be formed using the following methods. For example, after a photosensitive layer is formed and a photo-mask is positioned on the photosensitive layer, the photosensitive layer of portions, on which the emitter regions 121 and the BSF regions 172 will be formed, is exposed. Hence, a desired portion of the back passivation layer 192 is exposed. As a result, the plurality of emitter regions 121 and the plurality of BSF regions 172 are formed in the exposed portion of the back passivation layer 192. Further, after an emitter layer, for example, an amorphous silicon layer containing corresponding impurities is formed on the back passivation layer 192, a portion of the emitter layer is selectively removed to form the plurality of emitter regions 121 on the back passivation layer 192. Then, after a BSF layer, for example, an amorphous silicon layer containing corresponding impurities is formed on the exposed back passivation layer 192 and the emitter regions 121, a portion of the BSF layer is selectively removed to form the plurality of BSF regions 172. As described above, the emitter regions 121 and the BSF regions 172 may be formed on the back passivation layer 192 using the various methods.

Next, as shown in FIG. 3J, a conductive layer 40 containing a metal material is formed on the exposed back passivation layer 192, the plurality of emitter regions 121, and the plurality of BSF regions 172 using the PECVD method, etc. Then, a portion of the conductive layer 40 is sequentially removed through a wet etching process using a mask to form the electrode part 140 (refer to FIGS. 1 and 2) including the plurality of first and second electrodes 141 and 142.

Instead of the deposition process illustrated in FIG. 3J, a paste containing a metal material may be applied on the plurality of emitter regions 121 and the plurality of BSF regions 172 using a screen printing method, and then dried. Hence, the electrode part 140 including the plurality of first electrodes 141 positioned on the plurality of emitter regions 121 and the plurality of second electrodes 142 positioned on the plurality of BSF regions 172 may be formed.

Alternatively, all of the layers 191, 171, 130, 192, 121, 172, 141, and 142 formed on the substrate 110 may be formed using a physical vapor deposition method such as a sputtering method as well as a chemical vapor deposition method such as the PECVD method.

As above, because the layers formed on the substrate 110 are formed using the chemical vapor deposition method or the physical vapor deposition method performed at a low temperature of approximately 200° C., the solar cell 1 may be easily manufactured, and characteristics of each of the layers 191, 171, 130, 192, 121, 172, 141, and 142 may be prevented

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from being degraded at a high temperature. As a result, the efficiency of the solar cell 1, or manufacture thereof, is improved.

A solar cell 1a according to another example embodiment of the invention is described below with reference to FIGS. 4 and 5.

FIG. 4 is a partial perspective view of a solar cell according to another example embodiment of the invention. FIG. 5 is a cross-sectional view taken along line V-V of FIG. 4. In the following description, structures and components identical or equivalent to those illustrated in FIGS. 1 and 2 are designated with the same reference numerals, and a further description may be briefly made or may be entirely omitted.

The solar cell 1a shown in FIGS. 4 and 5 has the structure similar to the solar cell 1 shown in FIGS. 1 and 2.

More specifically, the solar cell 1a according to the example embodiment of the invention includes a substrate 110, a front passivation layer 191, an FSF region 171, and an anti-reflection layer 130 that are sequentially positioned on a front surface of the substrate 110, a back passivation layer 192a, a plurality of emitter regions 121, and a plurality of BSF regions 172 that are positioned on a back surface of the substrate 110, and an electrode part 140 including a plurality of first electrodes 141 respectively positioned on the plurality of emitter regions 121 and a plurality of second electrodes 142 respectively positioned on the plurality of BSF regions 172.

Unlike the solar cell 1 shown in FIGS. 1 and 2, in the solar cell 1a shown in FIGS. 4 and 5, the plurality of emitter regions 121 and the plurality of BSF regions 172 are positioned to directly contact the back surface of the substrate 110. Further, the back passivation layer 192a is positioned on the back surface of the substrate 110 excluding a formation portion of the emitter regions 121 and the BSF regions 172 from the back surface of the substrate 110. In other words, the configuration of the solar cell 1a shown in FIGS. 4 and 5 is substantially the same as the solar cell 1 shown in FIGS. 1 and 2 except a formation location of the back passivation layer 192a.

The back passivation layer 192a shown in FIGS. 4 and 5 has a thickness greater than the back passivation layer 192 shown in FIGS. 1 and 2, but is not limited thereto.

The back passivation layer 192a performs a passivation operation on and around the surface of the substrate 110 in the same manner as the back passivation layer 192, thereby reducing a loss amount of carriers caused to disappear by the defect on or around the surface of the substrate 110.

The back passivation layer 192a is formed of an insulating material such as silicon oxide (SiOx) and silicon nitride (SiNx). Thus, an electrical interference (for example, carrier movement) between the emitter region 121 and the BSF region 172 adjacent to each other is prevented or reduced by the back passivation layer 192a, and as a result, a loss amount of carriers is reduced. Further, light passing through the substrate 110 is prevented or reduced from being reflected inside the substrate 110, and thus an amount of light reflected to the outside is reduced.

As above, because the plurality of emitter regions 121 and the plurality of BSF regions 172 directly contact the back surface of the substrate 110, a transfer rate of carriers moving to the emitter regions 121 and the BSF regions 172 increases. Hence, the efficiency of the solar cell 1a is further improved.

A solar cell 1b according to another example embodiment of the invention is described below with reference to FIGS. 6 and 7.

FIG. 6 is a partial perspective view of a solar cell according to another example embodiment of the invention. FIG. 7 is a

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cross-sectional view taken along line VII-VII of FIG. 6. In the following description, structures and components identical or equivalent to those illustrated in FIGS. 1 and 2 are designated with the same reference numerals, and a further description may be briefly made or may be entirely omitted.

Similar to the solar cell 1 shown in FIGS. 1 and 2, the solar cell 1b shown in FIGS. 6 and 7 includes a substrate 110, a front passivation layer 191, an FSF region 171, and an anti-reflection layer 130 that are sequentially positioned on a front surface of the substrate 110, a back passivation layer 192c positioned on a back surface of the substrate 110, a plurality of emitter regions 121 and a plurality of BSF regions 172 positioned on the back passivation layer 192c, and an electrode part 140 including a plurality of first electrodes 141 respectively positioned on the plurality of emitter regions 121 and a plurality of second electrodes 142 respectively positioned on the plurality of BSF regions 172.

In the solar cell 1b shown in FIGS. 6 and 7, unlike the solar cell 1 shown in FIGS. 1 and 2, the back passivation layer 192c includes a plurality of first back passivation layers 1923 positioned between the substrate 110 and the plurality of emitter regions 121, and between the substrate 110 and the plurality of BSF regions 172; and a plurality of second back passivation layers 1924 positioned in other portions of the back surface of the substrate 110, i.e., between the plurality of emitter regions 121 and the plurality of BSF regions 172.

The first back passivation layers 1923 are formed of a conductive material such as amorphous silicon, and the second back passivation layers 1924 are formed of an insulating material such as silicon oxide (SiOx) and silicon nitride (SiNx). Hence, a conversion rate capable of converting unstable bonds existing at a contact surface between the back passivation layer 192c and the substrate 110 into stable bonds is improved. Further, an amount of carriers transferred to the emitter regions 121 or the BSF regions 172 increases because of conductive characteristics of the first back passivation layers 1923, and thus a carrier transfer rate increases. As a result, the efficiency of the solar cell 1b is further improved compared with the solar cell 1.

Further, as described above with reference to FIGS. 4 and 5, an electrical interference (for example, carrier movement) between the emitter region 121 and the BSF region 172 adjacent to each other is prevented or reduced by the second back passivation layers 1924, and as a result, the efficiency of the solar cell 1b is further improved.

In the solar cell 1b shown in FIGS. 6 and 7, thicknesses of the first and second back passivation layers 1923 and 1924 are substantially equal to each other, but may also be different from each other. For example, the thickness of the second back passivation layer 1924 may be greater than the thickness of the first back passivation layer 1923. In this instance, an electrical interference between the emitter region 121 and the BSF region 172 adjacent to each other is further reduced by the second back passivation layer 1924.

Although embodiments have been described with reference to a number of illustrative embodiments thereof, it should be understood that numerous other modifications and embodiments can be devised by those skilled in the art that will fall within the scope of the principles of this disclosure. More particularly, various variations and modifications are

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possible in the component parts and/or arrangements of the subject combination arrangement within the scope of the disclosure, the drawings and the appended claims. In addition to variations and modifications in the component parts and/or arrangements, alternative uses will also be apparent to those skilled in the art.

What is claimed is:

1. A solar cell, comprising:

a substrate that contains first impurities of a first conductive type, and is formed of a crystalline semiconductor;

a first passivation layer directly positioned on an incident surface of the substrate;

a first field region that is directly positioned on the first passivation layer, and contains second impurities of the first conductive type, the first field region being formed of amorphous silicon, amorphous silicon oxide, or amorphous silicon carbide;

an anti-reflection layer directly positioned on the first field region;

an emitter region that contains third impurities of a second conductive type opposite the first conductive type, is formed of a non-crystalline semiconductor, and is positioned on a non-incident surface of the substrate opposite the incident surface of the substrate;

a second passivation layer positioned on the non-incident surface of the substrate;

a second field region that is positioned at the non-incident surface of the substrate to be separated from the emitter region, wherein the second field region has the same conductive type as the first field region;

a first electrode electrically connected to the emitter region; and

a second electrode electrically connected to the second field region,

wherein a concentration of the second impurities contained in the first field region is 1×10^{16} atoms/cm³ to 1×10^{21} atoms/cm³,

the second passivation layer comprises first back passivation layers positioned between the substrate and the emitter region and between the substrate and the second field region, and a second back passivation layer exclusively and entirely positioned on the back surface of the substrate between the emitter region and the second field region,

the first back passivation layers are formed of amorphous silicon, and

the second back passivation layer is formed of at least one of silicon oxide (SiOx) and silicon nitride (SiNx).

2. The solar cell of claim 1, wherein the concentration of the second impurities contained in the first field region is higher than a concentration of the first impurities contained in the substrate.

3. The solar cell of claim 1, wherein the first field region has a thickness of 1 nm to 20 nm.

4. The solar cell of claim 1, wherein the first passivation layer has a thickness of 2 nm to 20 nm.

5. The solar cell of claim 1, wherein the concentration of the second impurities contained in the first field region is decreased towards the first passivation layer.

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